

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

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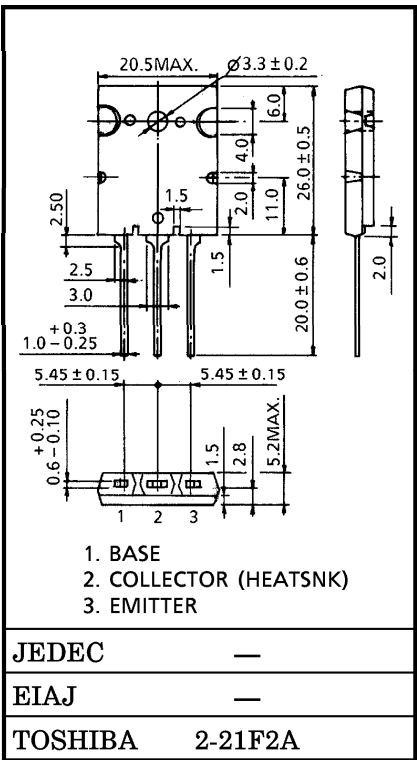
HORIZONTAL DEFLECTION OUTPUT FOR COLOR TV

Unit in mm

- High Voltage : $V_{CBO} = 2000\text{ V}$
- Low Saturation Voltage : $V_{CE(sat)} = 3\text{ V (Max.)}$
- High Speed : $t_f = 0.15\text{ }\mu\text{s (Typ.)}$

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	2000	V
Collector-Emitter Voltage		V_{CEO}	900	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current	DC	I_C	22	A
	Pulse	I_{CP}	44	
Base Current		I_B	11	A
Collector Power Dissipation (Tc = 25°C)		P_C	220	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55~150	°C



Weight : 9.75 g (Typ.)

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = 2000\text{ V}, I_E = 0$	—	—	1	mA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	100	μA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	900	—	—	V
DC Current Gain		$h_{FE(1)}$	$V_{CE} = 5\text{ V}, I_C = 2\text{ A}$	15	—	50	—
		$h_{FE(2)}$	$V_{CE} = 5\text{ V}, I_C = 9\text{ A}$	9.5	—	18.5	
		$h_{FE(3)}$	$V_{CE} = 5\text{ V}, I_C = 17\text{ A}$	4.8	—	9.0	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 17\text{ A}, I_B = 4.25\text{ A}$	—	—	3	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C = 17\text{ A}, I_B = 4.25\text{ A}$	—	—	1.3	V
Transition Frequency		f_T	$V_{CE} = 10\text{ V}, I_C = 0.1\text{ A}$	—	2	—	MHz
Collector Output Capacitance		C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	470	—	pF
Switching Time	Storage Time	t_{stg}	$I_{CP} = 8\text{ A}, I_{B1}(\text{end}) = 1\text{ A}$ $f_H = 32\text{ kHz}$	—	4.0	5.0	μs
	Fall Time	t_f		—	0.15	0.35	

